Calibration of the gain and measurement of the noise for the aPV25 electronics

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Experimental setup put in place at UVa to

 Measure the gain of two apv25 based readout electronics: Scalable Readout System (CERN, RD51) and MPD (INFN Italy for SBS)

• Measure the apv channels rms noise and estimation of the ENC from the apv gain measurement

Comparison of the performances of the two systems

APV25 MPD and SRS system

Multi Purpose Digitizer (MPD)

- P. Musico, INFN Italy
- More than 2.5K Channels at UVa

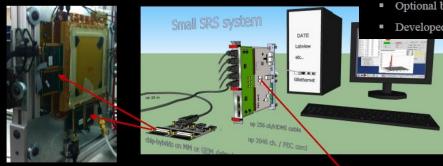
APV 25 Front End Card ⇒ MPD = ADC + APV controller APV 25 Front End Card ⇒ MPD = ADC + APV controller 75 mm Passive backplane

Main features:

SBS Weekly n

- 2 "active" components: Front-End Card and VME64x custom module (MPD=Multi Purpose Digitizer)
- HDMI Copper cables between front-end and VME
- Optional backplane acting as signal bus, electrical shielding, GND distributor and mechanical support
- Developed by INFN, manufactured by a commercial company

APV25-SRS Electronics @ UVa



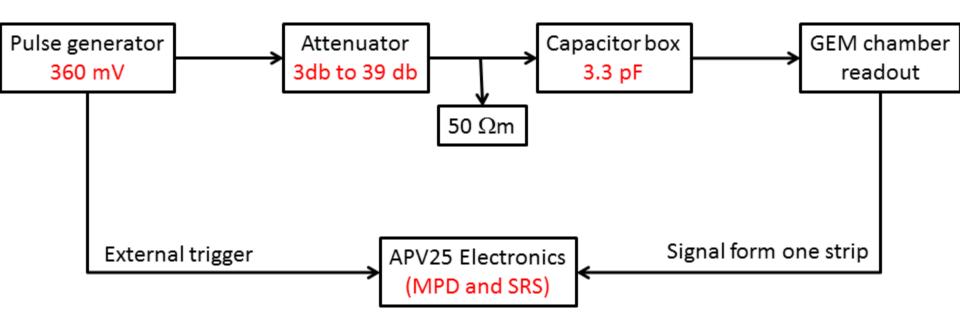
Scalable Readout System (SRS)

- Portable readout system developed by RD51 Collaboration (CERN)
- Successfully tested with APV25 chip (many users and experiments)
- APV25 cards, 1 ADC board, 1 Data Concentrator board
- Data transi<u>le 1 (0 ji) 1 ji 0 ji 0 ji</u> Ethernet via UDP (ALICE DAQ)
- Common platform for different chips (Bettle, VFAT, VMM1)

Scalable Readout System (SRS)

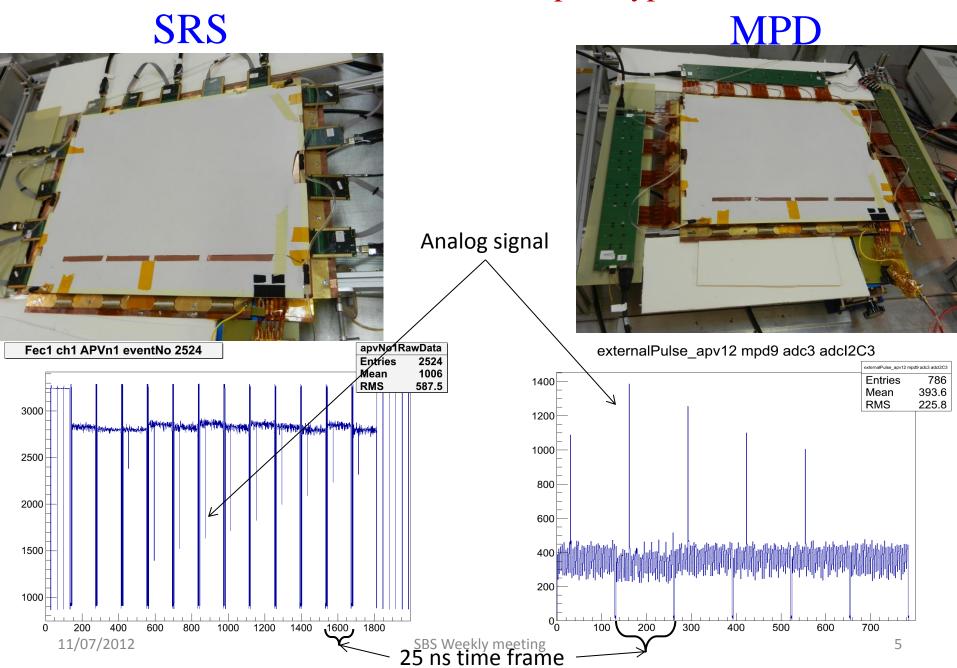
- H. Muller, CERN, RD51
- 2048 channels at Uva

APV25 Gain calibration setup

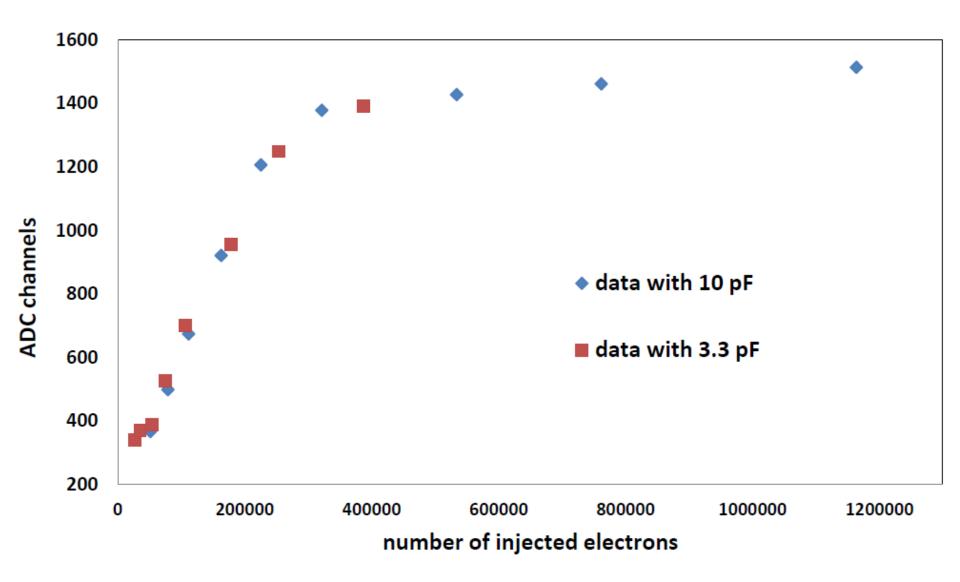


- Test pulse = 360 mV, Capacitor = 3.3 pF → Equivalent charges = 7.2 Million e-
- Injected charges = Equivalent charges / Attenuator attenuation 3dB to 39 db

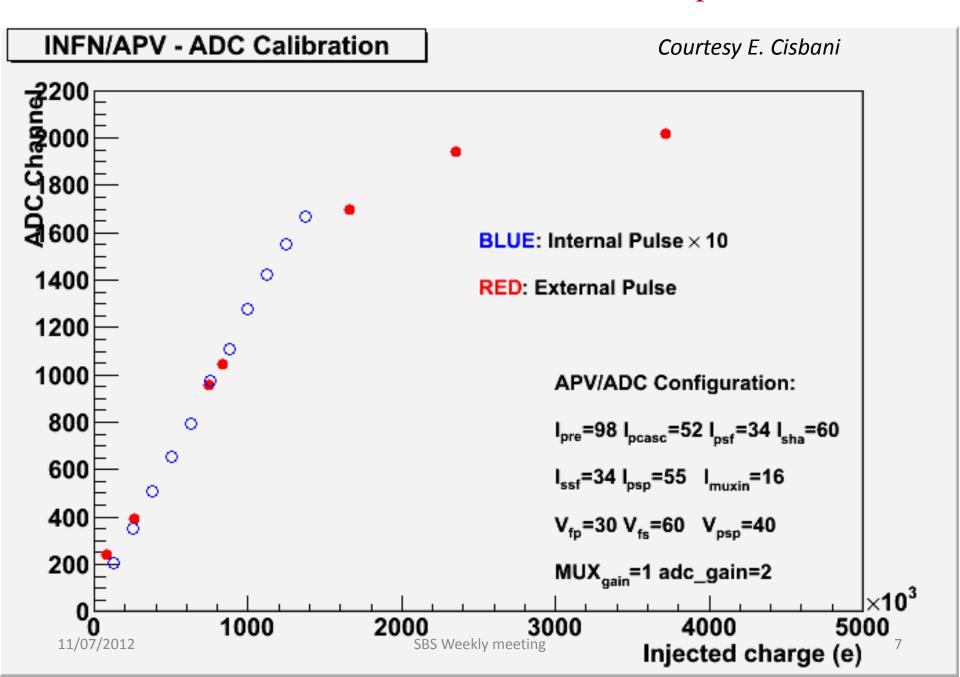
APV2 on SBS GEM prototype



APV25-SRS with external pulse



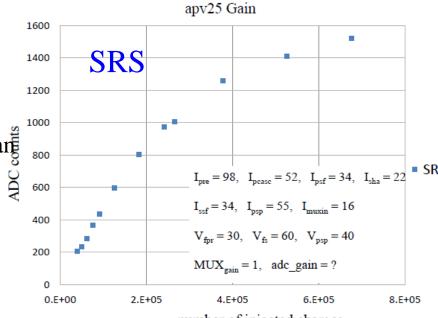
APV25-MPD with Internal & external pulse

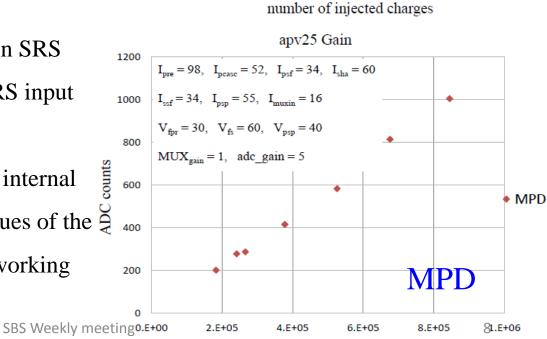


APV25 and ADC configuration for MPD and SRS systems

- We have almost the same configuration parameters for the two systems
- Different performances of the two electronics canges be related to some differences in hardware that Paolo has identified:
 - protecting diode in the VCC line of the INFN card
 - input capacitance 47 pF vs. 1 pF in SRS
 - 1 M Ω resistor to ground in the SRS input lines
 - external biasing in INFN card vs. internal biasing in SRS (this affect the values of the APV parameters for the optimal working point)

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number of injected charges

Apv25 Gain: MPD vs SRS

Gain calibration with 3.3pF and 10pF

